-	416	1 71 1 = 121	USPAT;	2003/06/12
	1	near5 ("10.sup.20")	US-PGPUB; EPO; JPO;	15:47
			DERWENT;	
			IBM TDB	
_	. 2	(p\$1type or n\$1type) near10 concentration	USPAT;	2003/06/12
	~	near5 ("10.sup.20") near10 nitride	US-PGPUB;	15:54
		, and a property of the second	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1436	(p\$1type or n\$1type) near10 concentration	USPAT;	2003/06/12
		same nitride	US-PGPUB;	15:49
			EPO; JPO; DERWENT;	
			IBM TDB	
_	327	(n\$1type) near10 concentration near10 (si	USPAT;	2003/06/12
	32,	or silicon) same nitride	US-PGPUB;	15:50
			EPO; JPO;	
	·		DERWENT;	
			IBM_TDB	
-	3	(n\$1type) near10 concentration near10 (si	USPAT;	2003/06/12
		or silicon) same nitride and 117/\$4.ccls.	US-PGPUB;	15:51
			EPO; JPO;	
			DERWENT; IBM TDB	
_	137	(n\$1type) near10 concentration near10 (si	USPAT;	2003/06/12
	13/	or silicon) same (gallium near2 nitride	US-PGPUB;	15:51
		or gan)	EPO; JPO;	
		,,	DERWENT;	
			IBM TDB	
-	112	(n\$1type) near10 concentration near10 (si	USPAT;	2003/06/12
		or silicon) near10 (gallium near2 nitride	US-PGPUB;	15:52
		or gan)	EPO; JPO;	
			DERWENT;	
l_	3	(p\$1type or n\$1type) near10 concentration	IBM_TDB USPAT;	2003/06/12
-	3	near5 ("10.sup.21") near10 nitride	US-PGPUB;	15:54
		nears (10.5ap.21) nearro metrae	EPO; JPO;	13.31
			DERWENT;	
			IBM_TDB	
-	10	(p\$1type or n\$1type) near10 concentration	USPĀT;	2003/06/12
		near5 ("10.sup.21") same nitride	US-PGPUB;	15:55
			EPO; JPO;	
			DERWENT;	
_	143	(p\$1type or n\$1type) near10 concentration	IBM_TDB	2003/06/12
]		near5 ("10.sup.21")	US-PGPUB;	15:58
1		· /	EPO; JPO;	' - '
			DERWENT;	
			IBM_TDB	
-	478	(p\$1type or n\$1type) near10 concentration	USPAT;	2003/06/12
[same (gallium adj nitride or gan)	US-PGPUB;	15:59
			EPO; JPO; DERWENT;	
.		•	IBM TDB	
_	359	(p\$1type or n\$1type) near10 concentration	USPAT;	2003/06/12
		near10 (gallium adj nitride or gan)	US-PGPUB;	16:19
			EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
] -	33	((p\$1type or n\$1type) near10	USPAT;	2003/06/12
]		concentration near10 (gallium adj nitride	US-PGPUB;	16:10
		or gan)) and 117\$4.ccls.	EPO; JPO; DERWENT;	
			IBM TDB	
_	24	(p\$1type or n\$1type) near10 concentration	USPAT;	2003/06/12
		near10 (gallium adj nitride or gan)	US-PGPUB;	16:07
		near10 more	EPO; JPO;	.
			DERWENT;	·
			IBM TDB	

				10000 /06 /10
-	169		USPAT;	2003/06/12
		near10 (gallium adj nitride or gan)	US-PGPUB;	16:07
		near10 high\$4	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
l	196	((p\$1type or n\$1type) near10	USPAT;	2003/06/12
İ		concentration near10 (gallium adj nitride	US-PGPUB;	16:11
		or gan)) and 257\$4.ccls.	EPO; JPO;	.
			DERWENT;	
			IBM TDB	
_	2	6218269.pn.	USPAT;	2003/06/12
	_	•	US-PGPUB;	16:14
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	5578839.pn.	USPAT;	2003/06/12
	-	- 00,000.F	US-PGPUB;	16:15
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	5	(p\$1type or n\$1type) near10 concentration	USPAT;	2003/06/12
		near10 (gallium adj nitride or gan) same	US-PGPUB;	16:19
1		(superlattice)	EPO; JPO;	
		(Superince)	DERWENT;	
			IBM TDB	
			TOM IND	